

M74HC123

DUAL RETRIGGERABLE MONOSTABLE MULTIVIBRATOR

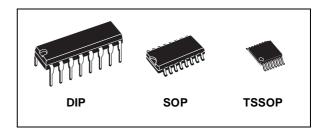
- HIGH SPEED : t_{PD} = 23 ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION: STAND BY STATE : I_{CC}=4µA (MAX.) at T_A=25°C ACTIVE STATE : I_{CC}=200µA (MAX.) at V_{CC} = 5V
- HIGH NOISE IMMUNITY:
 V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- WIDE OUTPUT PULSE WIDTH RANGE : t_{WOUT} = 120 ns ~ 60 s OVER AT V_{CC} = 4.5 V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 123

DESCRIPTION

The M74HC123 is an high speed CMOS MONOSTABLE MULTIVIBRATOR fabricated with silicon gate C²MOS technology.

There are two trigger inputs, A INPUT (negative edge) and B INPUT (positive edge). These inputs are valid for slow rising/falling signals, (tr=tf=l sec). The device may also be triggered by using the CLR input (positive-edge) because of the Schmitt-trigger input; after triggering the output maintains the MONOSTABLE state for the time

PIN CONNECTION AND IEC LOGIC SYMBOLS



ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC123B1R	
SOP	M74HC123M1R	M74HC123RM13TR
TSSOP		M74HC123TTR

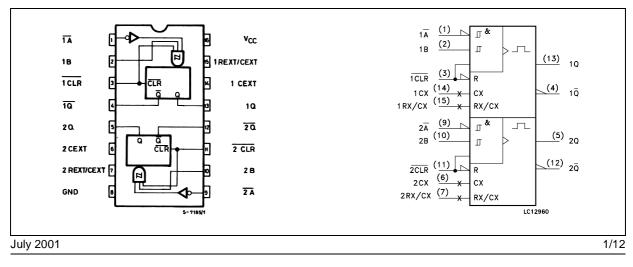
period determined by the external resistor Rx and capacitor Cx. When $Cx \ge 10$ nF and $Rx \ge 10$ K Ω , the output pulse width value is approximatively given by the formula : tW(OUT) = K · Cx · Rx. (K \cong 0.45).

Taking $\overrightarrow{\text{CLR}}$ low breaks this MONOSTABLE STATE. If the next trigger pulse occurs during the MONOSTABLE period it makes the MONOSTABLE period longer. Limit for values of Cx and Rx : Cx : NO LIMIT

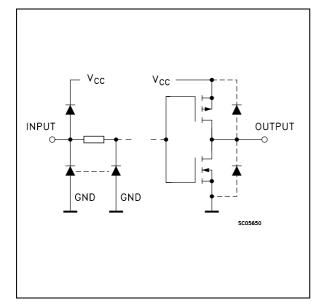
 $\text{Rx}:\text{V}_{\text{cc}}~<~3.0\text{V}~5\text{K}\Omega$ to $1\text{M}\Omega$

 $V_{cc} \ge 3.0V \ 1K\Omega \text{ to } 1M\Omega$

All inputs are equipped with protection circuits against static discharge and transient excess voltage.



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

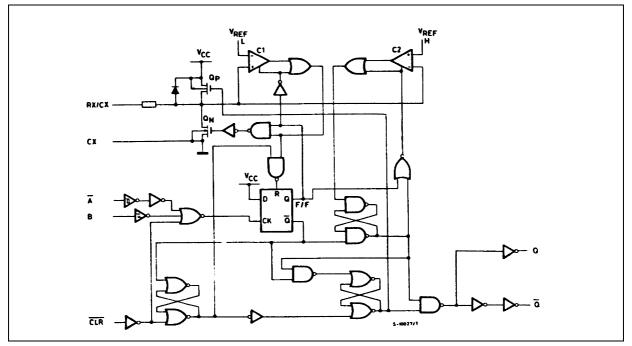
PIN No	SYMBOL	NAME AND FUNCTION
1,9	1Ā, 2Ā	Trigger Inputs (Negative Edge Triggered)
2, 10	1B, 2B	Trigger Inputs (Positive Edge Triggered)
3, 11	1 <u>CLR</u> 2 CLR	Direct Reset LOW and trigger Action at Positive Edge
4, 12	1Q, 2Q	Outputs (Active Low)
7	2R _X /C _X	External Resistor Capacitor Connection
13, 5	1Q, 2Q	Outputs (Active High)
14, 6	1C _X 2C _X	External Capacitor Connection
15	1R _X /C _X	External Resistor Capacitor Connection
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

TRUTH TABLE

	INPUTS		ουτι	PUTS	NOTE			
Ā	В	CLR	Q	Q	NOTE			
	Н	Н			OUTPUT ENABLE			
Х	L	Н	L	Н	INHIBIT			
Н	Х	Н	L	Н	INHIBIT			
L		Н			OUTPUT ENABLE			
L	Н				OUTPUT ENABLE			
Х	Х	L	L	Н	INHIBIT			

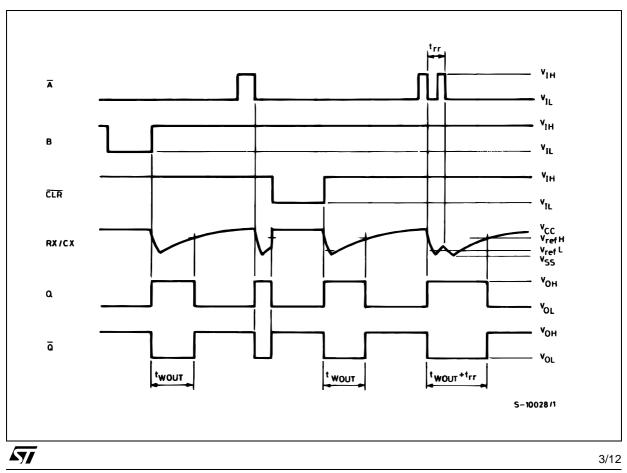
X : Don't Care

SYSTEM DIAGRAM

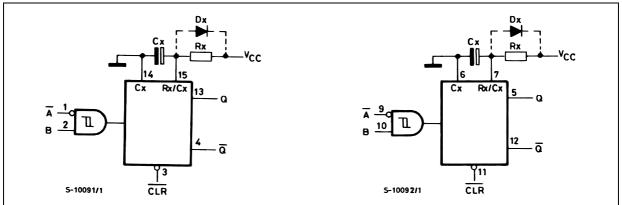


This logic diagram has not be used to estimate propagation delays

TIMING CHART



BLOCK DIAGRAM



(1) Cx, Rx, Dx are external components.(2) Dx is a clamping diode.

The external capacitor is charged to Vcc in the stand-by-state, i.e. no trigger. When the supply voltage is turned off Cx is discharged mainly trough an internal parasitic diode(see figures). If Cx is sufficiently large and Vcc decreases rapidly, there will be some possibility of damaging the I.C. with a surge current or latch-up. If the voltage supply filter capacitor is large enough and Vcc decrease slowly, the surge current is automatically limited and damage to the I.C. is avoided. The maximum forward current of the parasitic diode is approximately 20 mA. In cases where Cx is large the time taken for the supply voltage to fall to 0.4 Vcc can be calculated as follows : $t_f \ge (Vcc - 0.7) \times Cx/20mA$ In cases where t_f is too short an external clamping diode is required to protect the I.C. from the surge current.

FUNCTIONAL DESCRIPTION

STAND-BY STATE

The external capacitor, Cx, is fully charged to Vcc in the stand-by state. Hence, before triggering, transistor Qp and Qn (connected to the Rx/Cx node) are both turned-off. The two comparators that control the timing and the two reference voltage sources stop operating. The total supply current is therefore only leakage current.

TRIGGER OPERATION

Triggering occurs when :

1 st) A is "LOW" and B has a falling edge;

2 nd) B is "HIGH" and A has a rising edge;

3 rd) A is "LOW" and B is HIGH and C1 has a rising edge;

After the multivibrator has been retriggered comparator C1 and C2 start operating and Qn is turned on. Cx then discharges through Qn. The voltage at the node R/C external falls.

When it reaches V_{REFL} the output of comparator C1 becomes low. This in turn reset the flip-flop and Qn is turned off.

At this point C1 stops functioning but C2 continues to operate.

The voltage at R/C external begins to rise with a time constant set by the external components Rx, Cx.

Triggering the multivibrator causes Q to go high after internal delay due to the flip-flop and the gate. Q remains high until the voltage at R/C external rises again to V_{REFH} . At this point C2 output goes low and O goes low. C2 stop operating. That means that after triggering when the voltage R/C external returns to V_{RFFH} the multivibrator has returned to its MONOSTABLE STATE. In the case where $Rx \cdot Cx$ are large enough and the discharge time of the capacitor and the delay time in the I.C. can be ignored, the width of the output pulse tw (out) is as follows :

$tW(OUT) = 0.45 Cx \cdot Rx$

RE - TRIGGERED OPERATION

When a second trigger pulse follows the first its effect will depend on the state of the multivibrator. If the capacitor Cx is being charged the voltage level of R/C external falls to V_{REFL} again and Q remains High i.e. the retrigger pulse arrives in a time shorter than the period Rx · Cx seconds, the capacitor charging time constant. If the second trigger pulse is very close to the initial trigger pulse it is ineffective ; i.e. the second trigger must arrive in the capacitor discharge cycle to be ineffective; Hence the minimum time for a second trigger to be effective depends on Vcc and Cx

RESET OPERATION

CL is normally high. If CL is low, the trigger is not effective because Q output goes low and trigger control flip-flop is reset.

Also transistor Op is turned on and Cx is charged quickly to Vcc. This means if CL input goes low the IC becomes waiting state both in operating and non operating state.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
Ι _{ΙΚ}	DC Input Diode Current	± 20	mA
Ι _{ΟΚ}	DC Output Diode Current	± 20	mA
Ι _Ο	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
PD	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied (*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
t _r , t _f		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns
Сх	External Capacitor		NO LIMITATION	pF
Rx	External Resistor	Vcc < 3V	5K to 1M	Ω
INĂ		Vcc <u>></u> 3V	1K to 1M	52

The Maximum allowable values of Cx and Rx are a function of leakage of capacitor Cx, the leakage of device and leakage due to the board layout and surface resistance. Susceptibility to externally induced noise may occur for $Rx > 1M\Omega$

DC SPECIFICATIONS

		٦	Test Condition				Value				
Symbol	Parameter	v _{cc}		т	A = 25°	C	-40 to	85°C	-55 to 125°C		Unit
		(Ŭ)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
VIH	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V _{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V _{OH}	High Level Output	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		
	Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I	Input Leakage Current	6.0	$V_{I} = V_{CC} \text{ or } GND$			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	6.0	$V_{I} = V_{CC} \text{ or } GND$			4		40		80	μΑ
I _{CC} ,	Active State	2.0	$V_{I} = V_{CC} \text{ or } GND$		45	200		260		320	μΑ
	Supply Current (1)	4.5	Pin 7 or 15		500	600		780		960	μΑ
		6.0	$V_{IN} = V_{CC}/2$		0.7	1		1.3		1.6	mA

(1) : Per Circuit

		Г	est Condition				Value				
Symbol	Parameter	v _{cc}		Т	A = 25°	°C	-40 to	85℃	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110	
	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay	2.0			102	210		265		315	
	Time	4.5			29	42		53		63	ns
	(A , B - Q, Q)	6.0			22	36		45		54	
t _{PLH} t _{PHL}	Propagation Delay	2.0			102	235		295		355	
	Time(CLR	4.5			31	47		59		71	ns
	TRIGGER - Q, \overline{Q})	6.0			23	40		50		60	
t _{PLH} t _{PHL}	Propagation Delay	2.0			68	160		200		240	
	Time	4.5			20	32		40		48	ns
	$(\overline{\text{CLR}} - \text{Q}, \overline{\text{Q}})$	6.0			16	27		34		41	
t _{WOUT}	Output Pulse Width	2.0	0 400 - 5		1.4						
		4.5	Cx = 100 pF Rx = 10KΩ		1.2						μs
		6.0	KX = 10K22		1.1						
		2.0	0.045		4.6						
		4.5	Cx = 0.1μF Rx = 100KΩ		4.4						ms
		6.0	$\mathbf{K}\mathbf{X} = 100\mathbf{K}22$		4.3						
Δt_{WOUT}	Output Pulse Width Error Between Circuits in Same Package				±1						%
t _{W(H)}	Minimum Pulse	2.0				75		95		110	
t _{W(L)}	Width	4.5				15		19		22	ns
		6.0				13		16		19	
t _{W(L)}	Minimu <u>m P</u> ulse	2.0				75		95		110	
	Width (CLR)	4.5				15		19		22	ns
		6.0				13		16		19	
t _{rr}	Minimum Retrigger	2.0	0 400 - 5		325						
	Time	4.5	Cx = 100 pF Rx = 10KΩ		108						ns
		6.0	1X = 10IX22		78						
		2.0	0		5						
		4.5	Cx = 0.1μF Rx = 100KΩ		1.4						μs
		6.0	110 - 1001122		1.2						

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

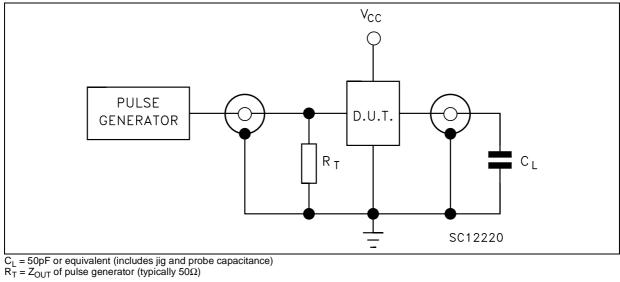
CAPACITIVE CHARACTERISTICS

		٦	Test Condition		Value						
Symbol	Parameter	v _{cc}		T	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			162						pF

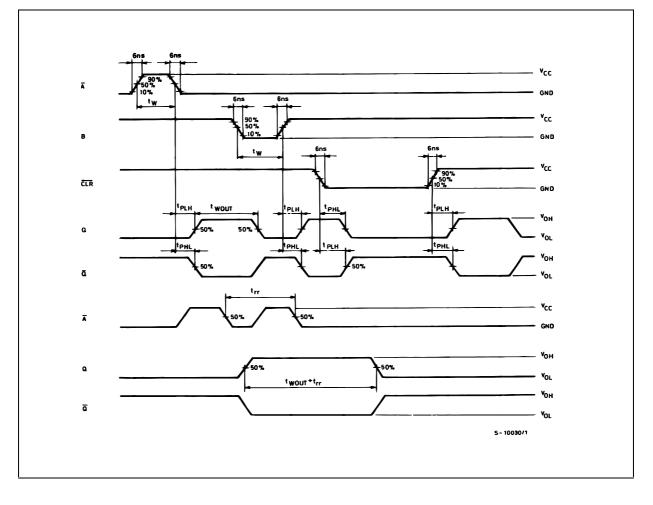
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}'$ Duty/100 + L_{C2}' per monostable) (I_{cc}' : Active Supply current) (Duty : %) 7/12

M74HC123

TEST CIRCUIT

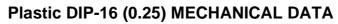


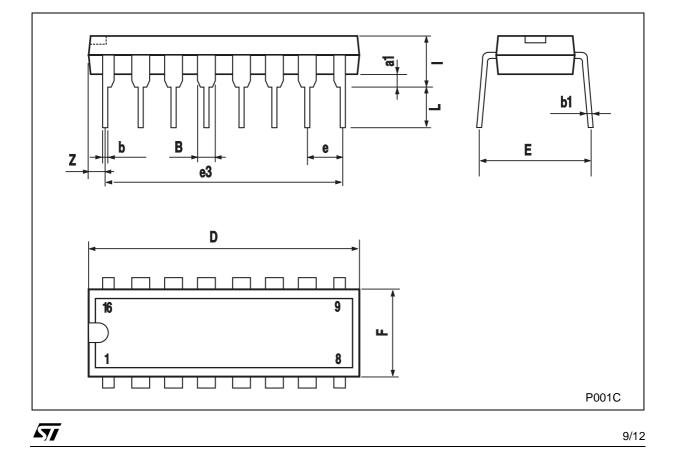
WAVEFORM : SWITCIHNG CHARACTERISTICS TEST WAVEFORM (f=1MHz; 50% duty cycle)



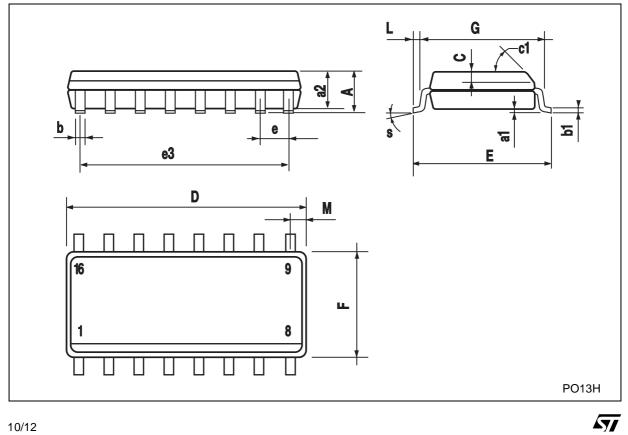
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DIM.		mm.		inch				
Dini.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			



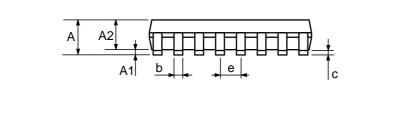


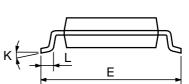
	SO-16 MECHANICAL DATA									
DIM		mm.			inch					
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.				
А			1.75			0.068				
a1	0.1		0.2	0.003		0.007				
a2			1.65			0.064				
b	0.35		0.46	0.013		0.018				
b1	0.19		0.25	0.007		0.010				
С		0.5			0.019					
c1		ł	45°	(typ.)		•				
D	9.8		10	0.385		0.393				
E	5.8		6.2	0.228		0.244				
е		1.27			0.050					
e3		8.89			0.350					
F	3.8		4.0	0.149		0.157				
G	4.6		5.3	0.181		0.208				
L	0.5		1.27	0.019		0.050				
М			0.62			0.024				
S		<u> </u>	8° (r	nax.)	•	+				

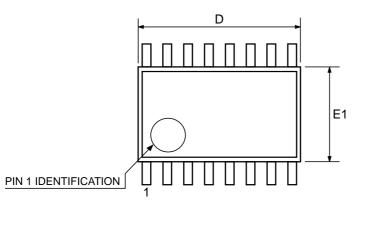


DIM.		mm.		inch					
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.			
А			1.2			0.047			
A1	0.05		0.15	0.002	0.004	0.006			
A2	0.8	1	1.05	0.031	0.039	0.041			
b	0.19		0.30	0.007		0.012			
С	0.09		0.20	0.004		0.0089			
D	4.9	5	5.1	0.193	0.197	0.201			
E	6.2	6.4	6.6	0.244	0.252	0.260			
E1	4.3	4.4	4.48	0.169	0.173	0.176			
е		0.65 BSC			0.0256 BSC				
К	0°		8°	0°		8°			
L	0.45	0.60	0.75	0.018	0.024	0.030			









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